

What is claimed is:

1. A semiconductor fabricating device, comprising:

a first semiconductor process unit installed in a production line that performs first semiconductor fabricating processes and that generates a process deteriorating gas during the first semiconductor fabricating processes; and

a second semiconductor process unit installed in the production line that performs second semiconductor fabricating processes dependent on the first semiconductor fabricating processes, the second semiconductor fabricating processes being susceptible to operational failures if exposed to the process deteriorating gas,

wherein the second semiconductor process unit is installed at a higher level than the first semiconductor process unit, and

wherein clean air flows downward over the first and second semiconductor process units to carry the process deteriorating gas away from the second semiconductor process unit.

2. The semiconductor fabricating device of claim 1, wherein the first semiconductor process unit comprises an adhesion unit having an adhesion chamber that supplies an adhesion enhancing material that reinforces adhesion between a wafer and a photoresist layer when the photoresist layer is deposited onto the wafer, and

wherein the second semiconductor process unit comprises a bake unit that bakes the wafer having the photoresist layer formed thereon.

1 3. The semiconductor fabricating device of claim 1, wherein the process
2 deteriorating gas is ammonia (NH₄).

1 4. A semiconductor fabricating device, comprising:
2 a first semiconductor process unit installed in a production line that performs first
3 semiconductor fabricating processes and that generates a process deteriorating gas during
4 the first semiconductor fabricating processes; and
5 a second semiconductor process unit installed in the production line that performs
6 second semiconductor fabricating processes dependent on the first semiconductor
7 fabricating processes, the second semiconductor fabricating processes being susceptible
8 to operational failures if exposed to the process deteriorating gas,
9 wherein the first semiconductor process unit is installed in a first position and the
10 second semiconductor process unit is installed at second position, and
11 wherein clean air flows from the second position to the first position to carry the
12 process deteriorating gas away from the second semiconductor process unit.

1 5. The semiconductor fabricating device of claim 4, wherein the first
2 semiconductor process unit comprises an adhesion unit having an adhesion chamber that
3 supplies an adhesion enhancing material that reinforces adhesion between a wafer and a

4 photoresist layer when the photoresist layer is deposited onto the wafer, and
5 wherein the second semiconductor process unit comprises a bake unit that bakes
6 the wafer having the photoresist layer formed thereon.

1 6. The semiconductor fabricating device of claim 4, wherein the operational
2 deteriorating gas is ammonia (NH₄).

1 7. The semiconductor fabricating device of claim 4, wherein the second position is
2 at a higher location within the semiconductor fabricating device than the first position.

1 8. A method of fabricating a semiconductor device comprising:
2 performing first semiconductor fabricating processes at a first location, the first
3 semiconductor fabricating processes generating a process deteriorating gas;
4 performing second semiconductor fabricating processes that are dependent on the
5 first semiconductor fabricating processes at a second location, the second semiconductor
6 fabricating processes being susceptible to operational failures upon exposure to the
7 process deteriorating gas; and
8 flowing clean air from the second location to the first location to carry the process
9 deteriorating gas away from the second location.

1 9. The method of fabricating a semiconductor device of claim 8, wherein the first
2 semiconductor fabricating processes comprise supplying an adhesion enhancing material
3 that reinforces adhesion between a wafer and a photoresist layer when the photoresist
4 layer is deposited onto the wafer, and

5 wherein the second semiconductor fabrication processes comprise baking the
6 wafer having the photoresist layer thereon.

1 10. The method of fabricating a semiconductor device of claim 8, wherein the
2 process deteriorating gas is ammonia (NH₄).

1 11. The method of fabricating a semiconductor device of claim 8, wherein the
2 second location is higher than the first location.

1 12. The method of fabricating a semiconductor device of claim 8, wherein the
2 second semiconductor fabricating processes are performed after the first semiconductor
3 fabricating processes.